

IN THE CLAIMS:

Claims 4 and 17 have been cancelled. Claims 1-3, 4-16, and 18-21 have been amended herein. All of the pending claims 1 through 21 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A method for fabricating a mask comprising:
forming a substrate including:
a first layer of attenuating material over ~~said~~the substrate;
a second layer of attenuating material over ~~said~~the first layer of attenuating material; and
an opaque layer over ~~said~~the second layer of attenuating material;
etching ~~said~~the substrate to form at least one completely transmissive region;
etching ~~said~~the substrate to form at least one slightly attenuated region, ~~said~~the etching including
forming a ~~second~~-patterned resist over ~~said~~the substrate; and
etching ~~said~~the substrate to form at least one highly attenuated region.
2. (Currently Amended) The method according to claim 1, wherein etching ~~said~~the substrate to form ~~said~~the at least one completely transmissive region comprises forming a first patterned resist over ~~said~~the opaque layer of ~~said~~the substrate and etching ~~said~~the substrate to form a plurality of isolated completely transmissive regions and a plurality of ~~elose~~ely-~~close~~ly spaced completely transmissive regions.
3. (Currently Amended) The method according to claim 2, wherein etching ~~said~~the substrate to form ~~said~~the at least one slightly attenuated region comprises removing portions of ~~said~~the opaque layer and ~~said~~the second layer of attenuating material to form a plurality of slightly attenuated regions, each of ~~said~~the plurality of slightly attenuated regions being positioned at an edge defining one of ~~said~~the plurality of isolated completely transmissive regions.

4. (Deleted without prejudice)

5. (Currently Amended) The method according to claim 2, wherein etching ~~said~~the substrate to form ~~said~~the at least one highly attenuated region comprises removing portions of ~~said~~the opaque layer to form a plurality of highly attenuated regions, each of ~~said~~the plurality of highly attenuated regions being positioned at an edge defining one of ~~said~~the plurality of ~~elose~~ly-~~close~~ly spaced completely transmissive regions.

6. (Currently Amended) The method according to claim 5, wherein etching ~~said~~the substrate to form ~~said~~the plurality of highly attenuated regions comprises forming a third patterned resist over ~~said~~the substrate.

7. (Currently Amended) The method according to claim 1, wherein ~~provid~~forming ~~said~~the substrate further comprises ~~provid~~forming ~~said~~the substrate ~~comprising to include~~ an etch stop layer between ~~said~~the first layer of attenuating material and ~~said~~the second layer of attenuating material.

8. (Currently Amended) The method according to claim 7, wherein etching ~~said~~the substrate to form ~~said~~the at least one completely transmissive region comprises forming a first patterned resist over ~~said~~the opaque layer of ~~said~~the substrate and etching ~~said~~the substrate to form a plurality of isolated completely transmissive regions and a plurality of ~~elose~~ly-~~close~~ly spaced completely transmissive regions.

9. (Currently Amended) The method according to claim 8, wherein etching ~~said~~the substrate to form ~~said~~the at least one slightly attenuated region comprises removing portions of ~~said~~the opaque layer and ~~said~~the second layer of attenuating material in a single etch step to form a plurality of slightly attenuated regions, each of ~~said~~the plurality of slightly attenuated regions being positioned at an edge defining one of ~~said~~the plurality of isolated completely transmissive regions.

10. (Currently Amended) The method according to claim 9, wherein etching ~~said~~the substrate to form ~~said~~the at least one highly attenuated region comprises removing portions of ~~said~~the opaque layer to form a plurality of highly attenuated regions, each of ~~said~~the plurality of highly attenuated regions being positioned at an edge defining one of ~~said~~the plurality of ~~closely~~closely spaced completely transmissive regions.

11. (Currently Amended) The method according to claim 10, wherein etching ~~said~~the substrate to form ~~said~~the plurality of highly attenuated regions comprises forming a third patterned resist over ~~said~~the substrate.

12. (Currently Amended) A attenuated phase shift mask comprising:
a transparent substrate;
a plurality of isolated completely transmissive regions and a plurality of other regions;
a plurality of slightly attenuated regions, each of ~~said~~the plurality of slightly attenuated regions being formed at an edge defining one of ~~said~~the plurality of isolated completely transmissive regions;
a plurality of completely transmissive regions; and
a plurality of highly attenuated regions, each of ~~said~~the plurality of highly attenuated regions being formed at an edge defining one of ~~said~~the plurality of isolated completely transmissive regions, ~~said~~the plurality of highly attenuated regions comprising a first layer of attenuating material, a layer of etch stop material, and a second layer of attenuating material.

13. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, further comprising a plurality of opaque regions.

14. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 13, wherein ~~said~~the plurality of opaque regions comprise chromium.

15. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, wherein ~~said~~the transparent substrate comprises a material selected from a group consisting of quartz, fused silica, and glass.

16. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, wherein ~~said~~the plurality of slightly attenuated regions comprises a layer of attenuating material selected from a group consisting of chromium oxynitride and chromium fluoride.

17. (Deleted without prejudice)

18. (Currently Amended) The ~~attenuated~~ phase shift mask of claim ~~17~~ 12, wherein ~~said~~the first layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride and ~~said~~the second layer of attenuating material comprises molybdenum silicide oxynitride.

19. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, wherein ~~said~~the plurality of slightly attenuated regions comprises a layer of attenuating material and a layer of etch stop material.

20. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 19, wherein ~~said~~the layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride and ~~said~~the layer of etch stop material comprises silicon dioxide.

21. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, wherein ~~said~~the first layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride, ~~said~~the layer of etch stop material comprises silicon dioxide, and ~~said~~the second layer of attenuating material comprises molybdenum silicide oxynitride.